

V_{DSS}	1200V
$R_{DS(on)}$ (Typ.)	280mΩ
I_D	14A
P_D	108W

●Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating ; RoHS compliant

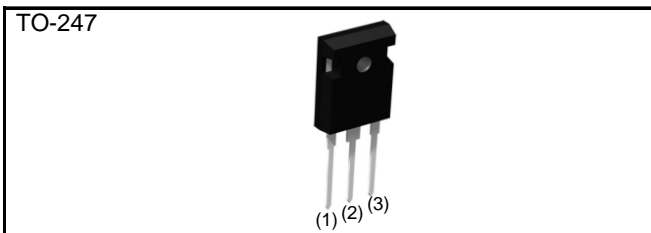
●Application

- Solar inverters
- DC/DC converters
- Switch mode power supplies
- Induction heating
- Motor drives

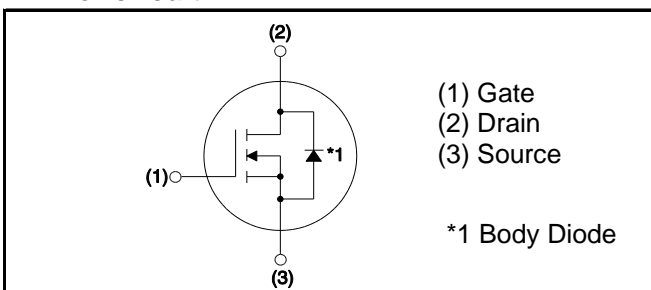
●Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	1200	V
Continuous drain current	$T_c = 25^\circ\text{C}$	I_D^{*1}	14	A
	$T_c = 100^\circ\text{C}$	I_D^{*1}	10	A
Pulsed drain current		$I_{D,pulse}^{*2}$	35	A
Gate - Source voltage (DC)		V_{GSS}	-6 to 22	V
Gate - Source surge voltage ($T_{surge} < 300\text{nsec}$)		$V_{GSS-surge}^{*3}$	-10 to 26	V
Power dissipation ($T_c = 25^\circ\text{C}$)		P_D	108	W
Junction temperature		T_j	175	$^\circ\text{C}$
Range of storage temperature		T_{stg}	-55 to +175	$^\circ\text{C}$

●Outline



●Inner circuit



●Packaging specifications

Type	Packaging	Tube
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	30
	Packing code	C
	Marking	SCT2280KE

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	1.07	1.39	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

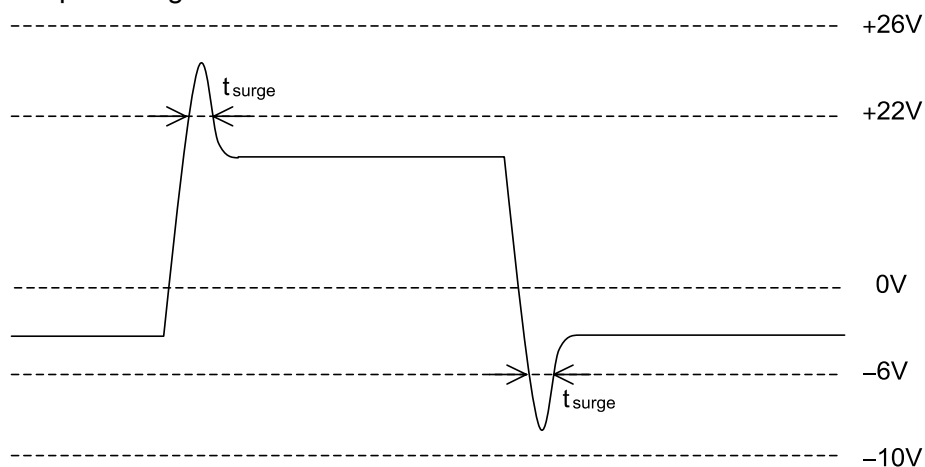
●Electrical characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 1mA$	1200	-	-	V
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 1200V, V_{GS} = 0V$	-	1	10	μA
		$T_j = 150^\circ\text{C}$	-	2	-	
Gate - Source leakage current	I_{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	-	-	100	nA
Gate - Source leakage current	I_{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 1.4mA$	1.6	2.8	4.0	V

*1 Limited only by maximum temperature allowed.

*2 $PW \leq 10\mu\text{s}$, Duty cycle $\leq 1\%$

*3 Example of acceptable Vgs waveform



*4 Pulsed

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Static drain - source on - state resistance	R _{DS(on)} ^{*4}	V _{GS} = 18V, I _D = 4A T _j = 25°C T _j = 125°C	- -	280 388	364 -	mΩ
Gate input resistance	R _G	f = 1MHz, open drain	-	17	-	Ω
Transconductance	g _{fs} ^{*4}	V _{DS} = 10V, I _D = 4A	-	1.4	-	S
Input capacitance	C _{iss}	V _{GS} = 0V	-	667	-	pF
Output capacitance	C _{oss}	V _{DS} = 800V	-	27	-	
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	5	-	
Effective output capacitance, energy related	C _{o(er)}	V _{GS} = 0V V _{DS} = 0V to 500V	-	41	-	pF
Turn - on delay time	t _{d(on)} ^{*4}	V _{DD} = 400V, V _{GS} = 18V	-	19	-	ns
Rise time	t _r ^{*4}	I _D = 4A	-	19	-	
Turn - off delay time	t _{d(off)} ^{*4}	R _L = 100Ω	-	47	-	
Fall time	t _f ^{*4}	R _G = 0Ω	-	29	-	
Turn - on switching loss	E _{on} ^{*4}	V _{DD} = 600V, I _D = 4A V _{GS} = 18V/0V R _G = 0Ω, L = 500μH	-	57	-	μJ
Turn - off switching loss	E _{off} ^{*4}	*E _{on} includes diode reverse recovery	-	20	-	

●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q _g ^{*4}	V _{DD} = 400V	-	36	-	nC
Gate - Source charge	Q _{gs} ^{*4}	I _D = 4A	-	9	-	
Gate - Drain charge	Q _{gd} ^{*4}	V _{GS} = 18V	-	12	-	
Gate plateau voltage	V _(plateau)	V _{DD} = 400V, I _D = 4A	-	9.8	-	V

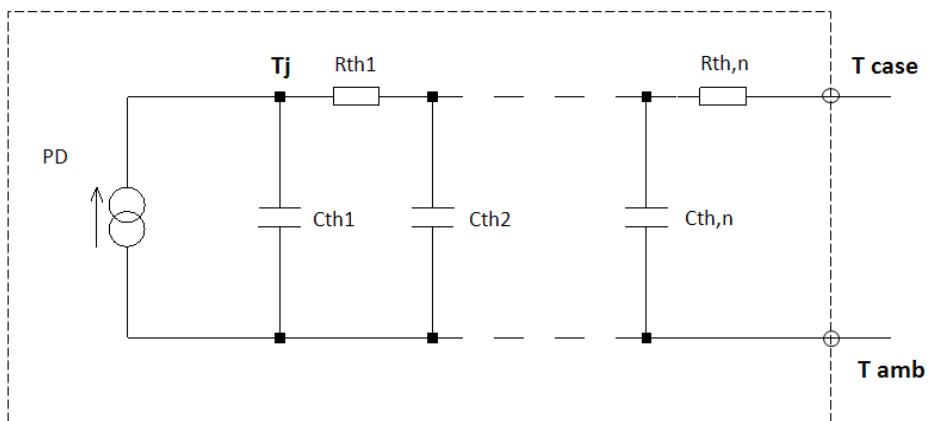
●Body diode electrical characteristics (Source-Drain) ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	I_S^{*1}	$T_c = 25^\circ\text{C}$	-	-	14	A
Inverse diode direct current, pulsed	I_{SM}^{*2}		-	-	35	A
Forward voltage	V_{SD}^{*4}	$V_{GS} = 0\text{V}, I_S = 4\text{A}$	-	4.0	-	V
Reverse recovery time	t_{rr}^{*4}	$I_F = 4\text{A}, V_R = 400\text{V}$ $di/dt = 160\text{A}/\mu\text{s}$	-	22	-	ns
Reverse recovery charge	Q_{rr}^{*4}		-	21	-	nC
Peak reverse recovery current	I_{rrm}^{*4}		-	2.0	-	A

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R_{th1}	100m	K/W
R_{th2}	662m	
R_{th3}	304m	

Symbol	Value	Unit
C_{th1}	861 μ	Ws/K
C_{th2}	2.84m	
C_{th3}	55.9m	



●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

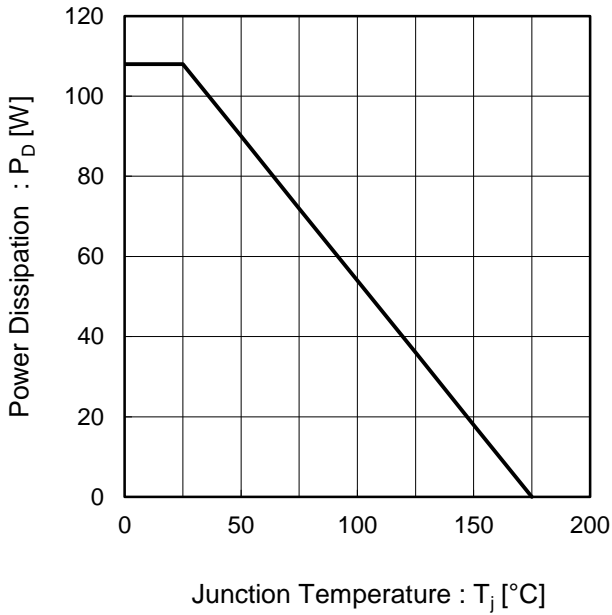


Fig.2 Maximum Safe Operating Area

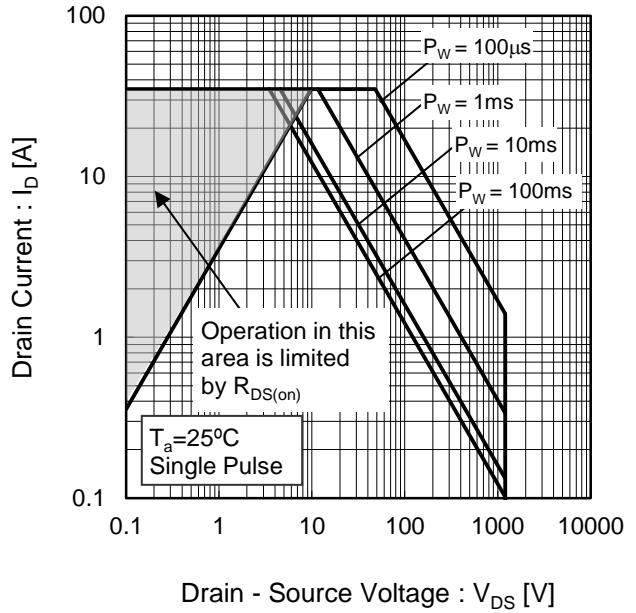
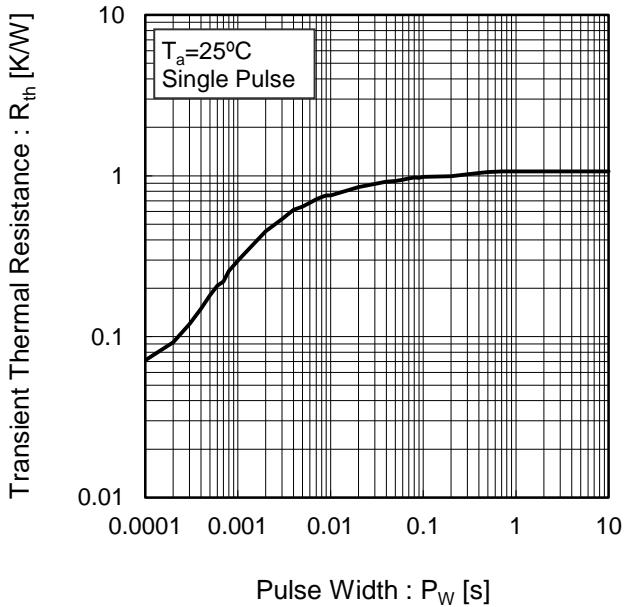


Fig.3 Typical Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Typical Output Characteristics(I)

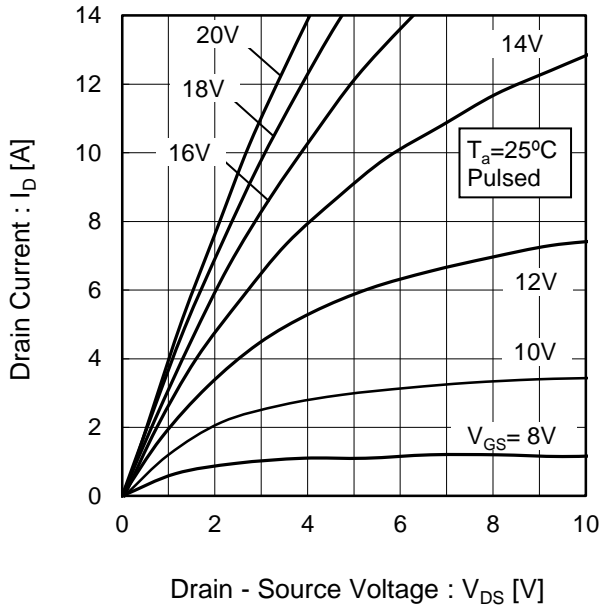


Fig.5 Typical Output Characteristics(II)

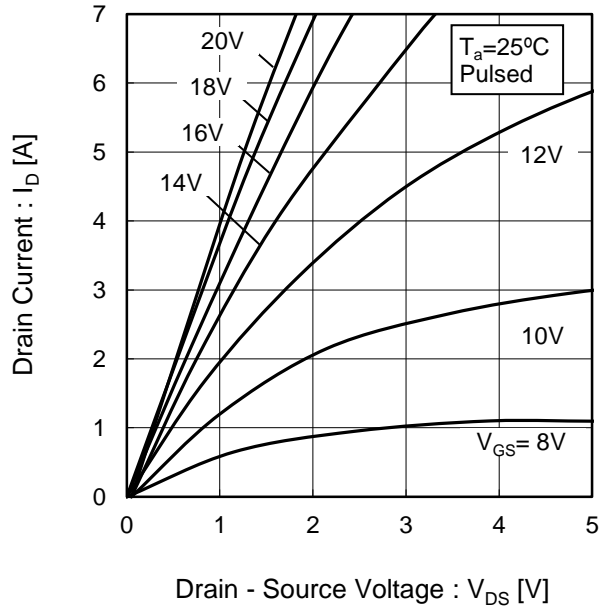


Fig.6 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(I)

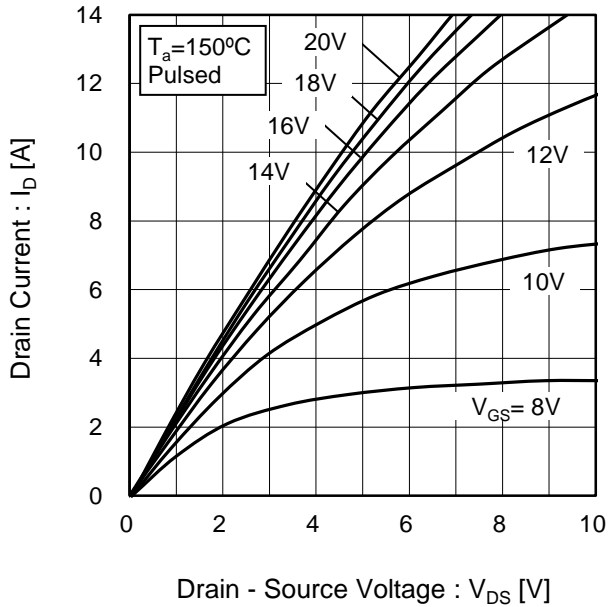
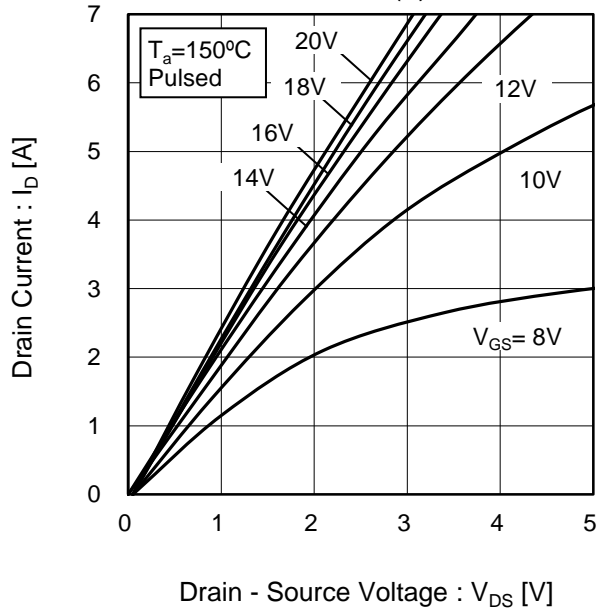


Fig.7 $T_j = 150^\circ\text{C}$ Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Typical Transfer Characteristics (I)

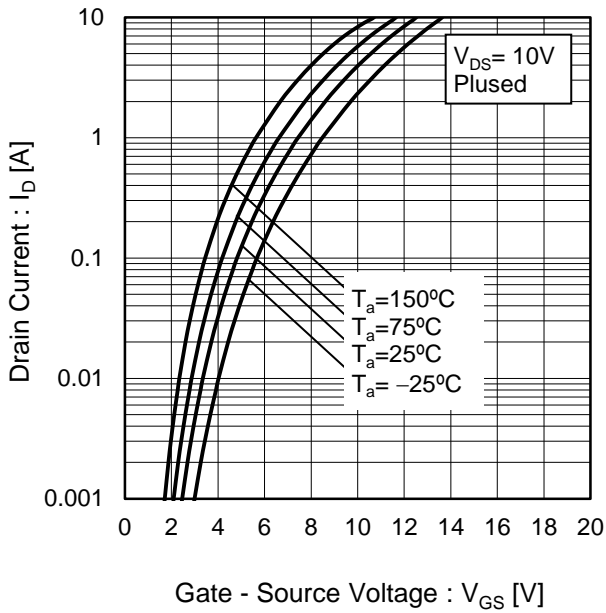


Fig.9 Typical Transfer Characteristics (II)

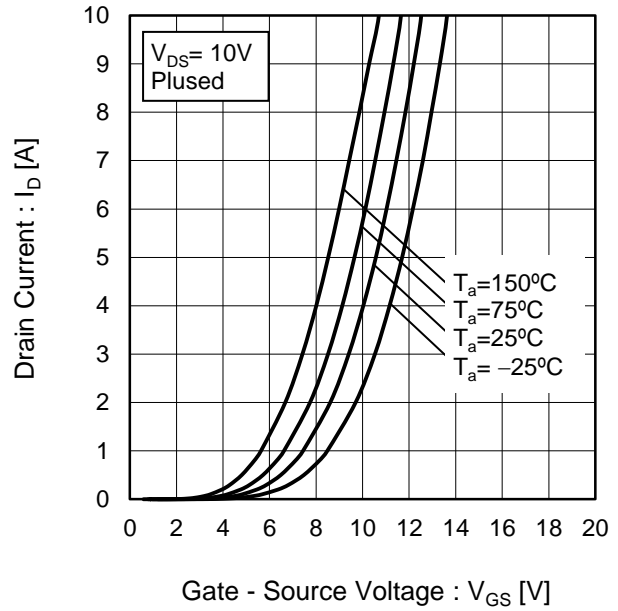


Fig.10 Gate Threshold Voltage vs. Junction Temperature

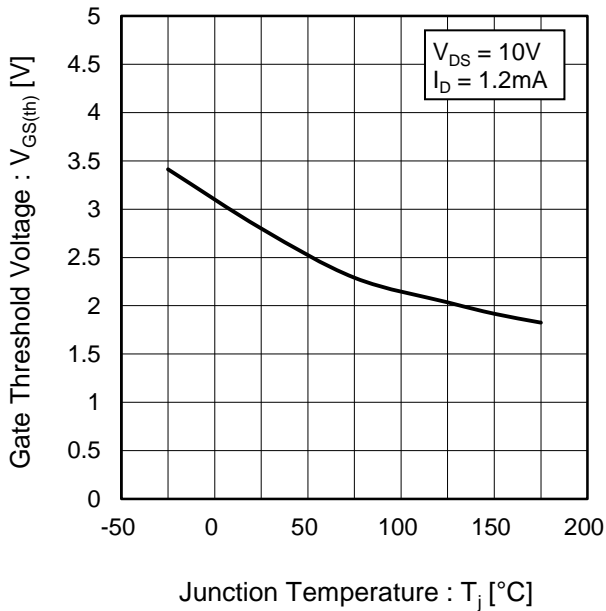
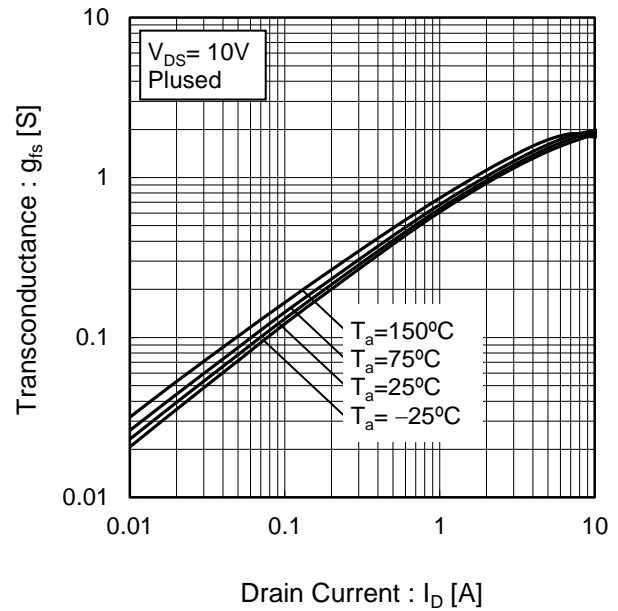


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

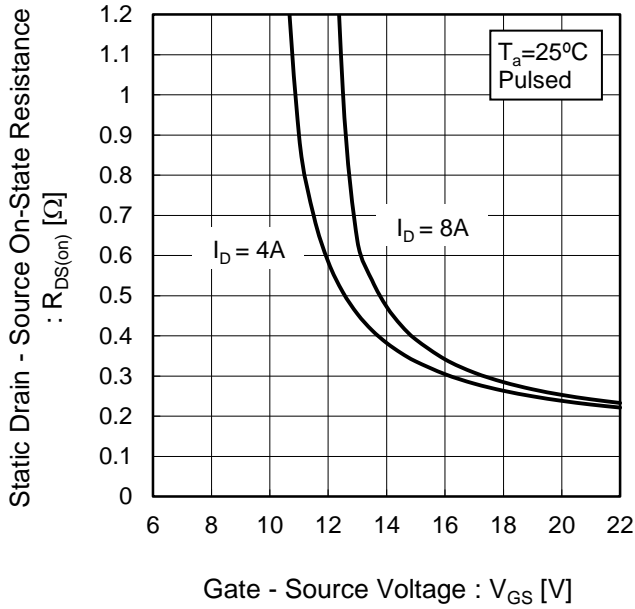


Fig.13 Static Drain - Source On - State Resistance vs. Junction Temperature

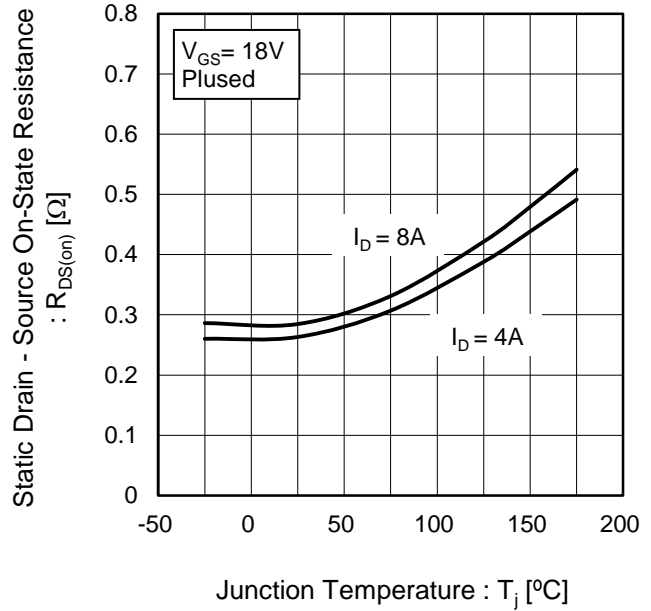
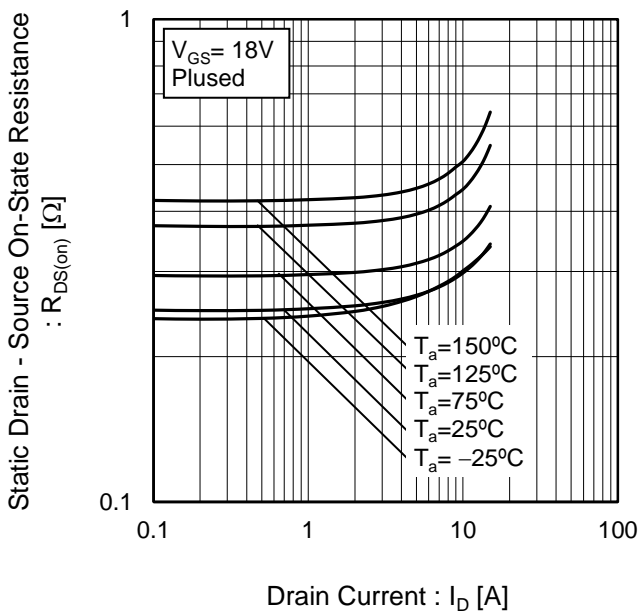


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current



●Electrical characteristic curves

Fig.15 Typical Capacitance vs. Drain - Source Voltage

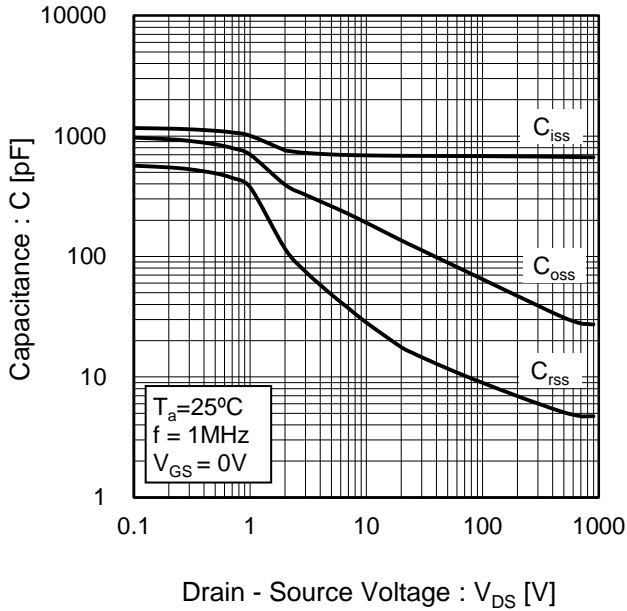


Fig.16 Coss Stored Energy

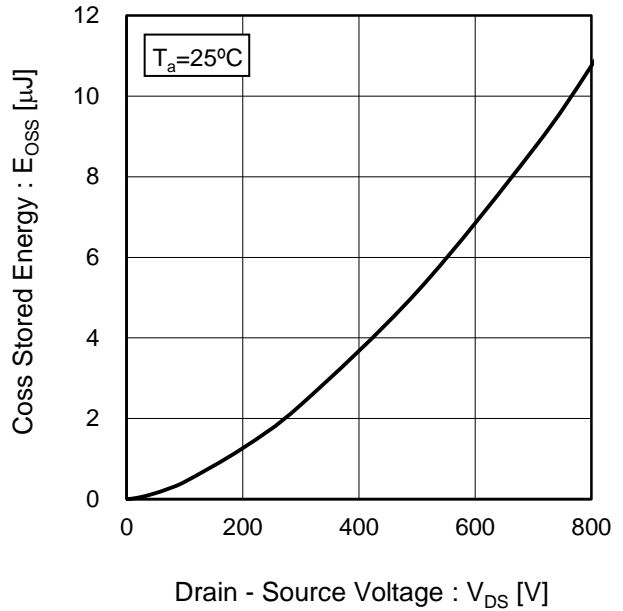


Fig.17 Switching Characteristics

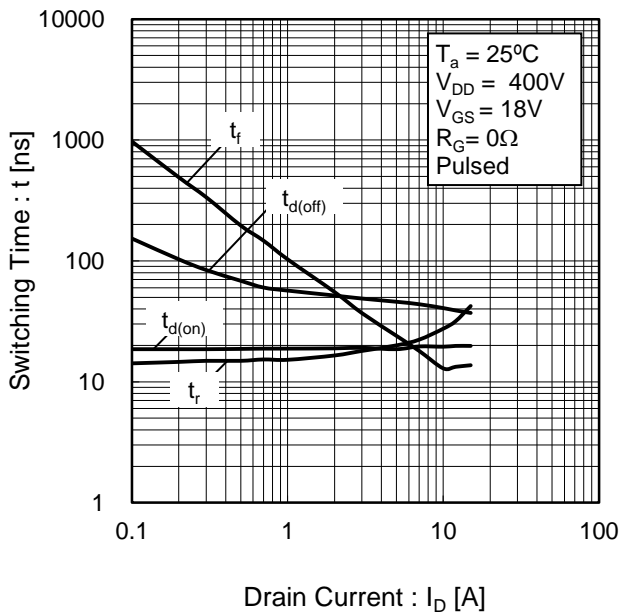
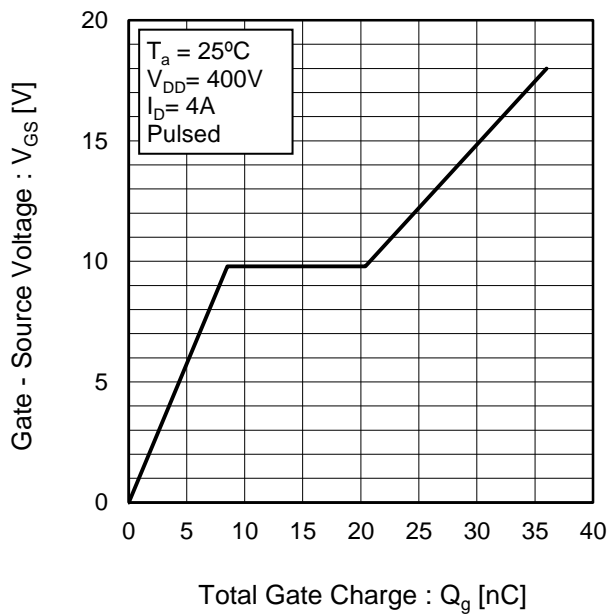


Fig.18 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.19 Typical Switching Loss vs. Drain - Source Voltage

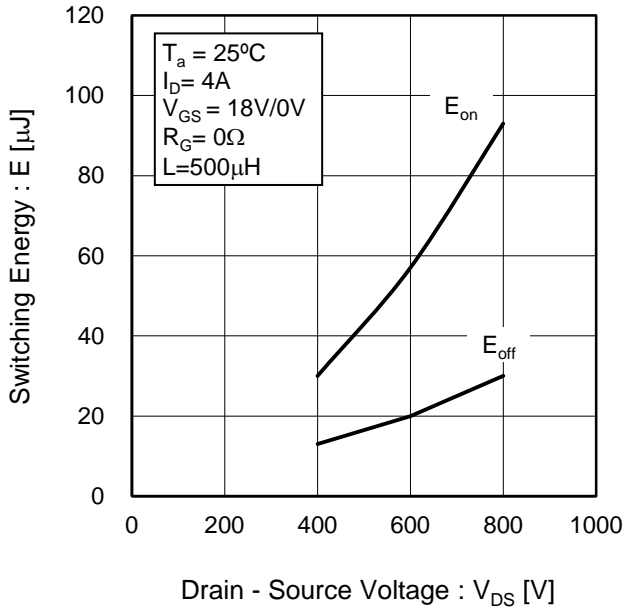


Fig.20 Typical Switching Loss vs. Drain Current

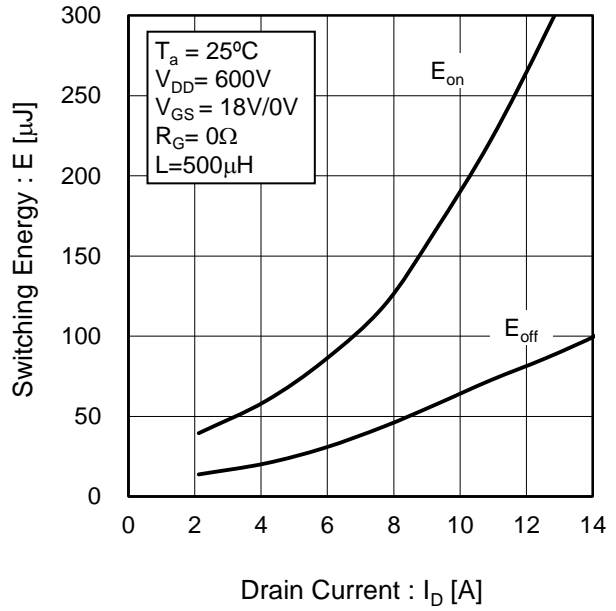
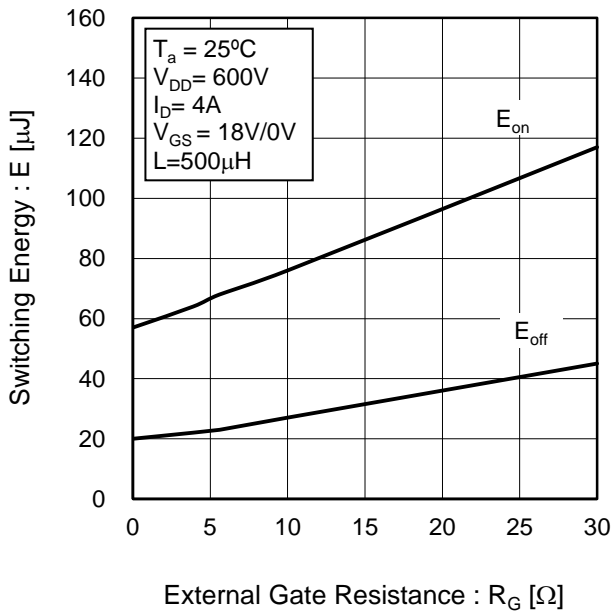


Fig.21 Typical Switching Loss vs. External Gate Resistance



●Electrical characteristic curves

Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

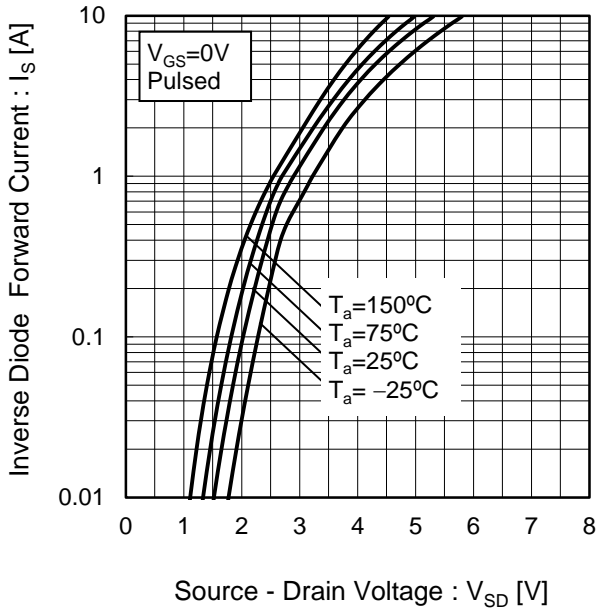
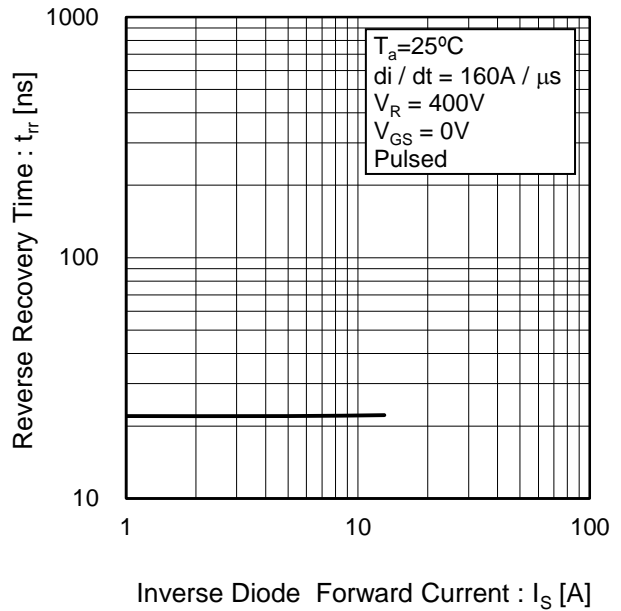


Fig.23 Reverse Recovery Time vs. Inverse Diode Forward Current



● Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

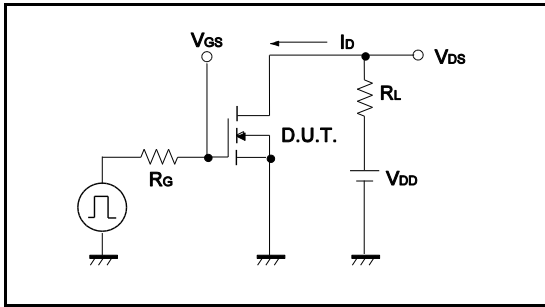


Fig.1-2 Switching Waveforms

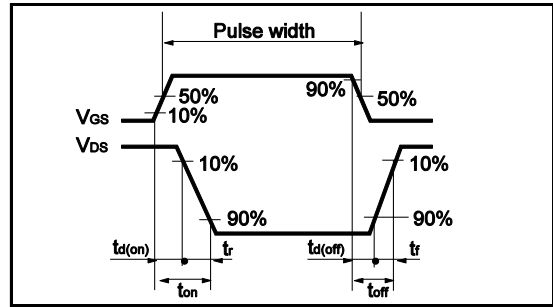


Fig.2-1 Gate Charge Measurement Circuit

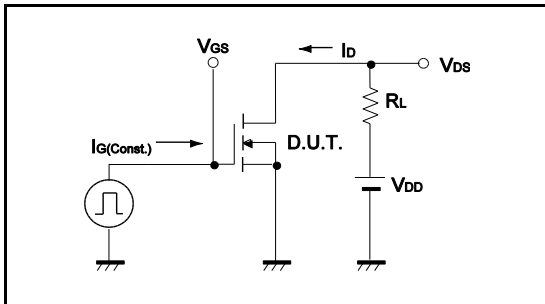


Fig.2-2 Gate Charge Waveform

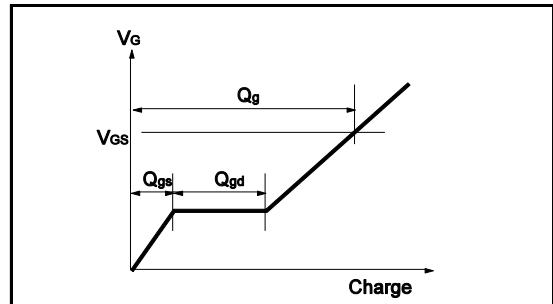


Fig.3-1 Switching Energy Measurement Circuit

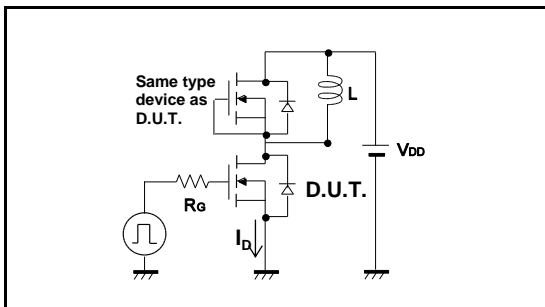


Fig.3-2 Switching Waveforms

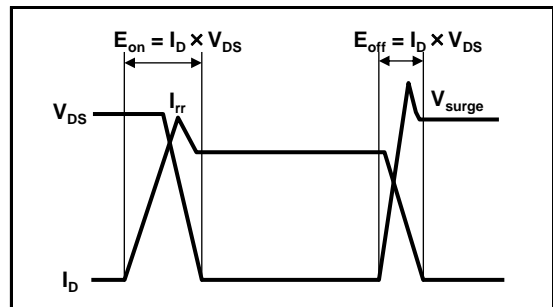


Fig.4-1 Reverse Recovery Time Measurement Circuit

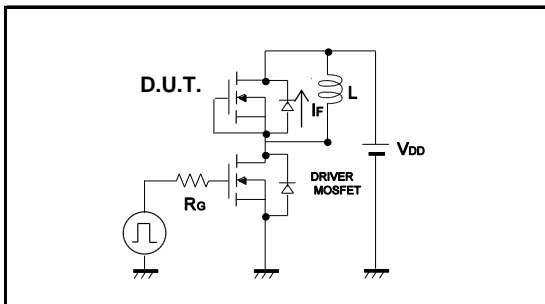
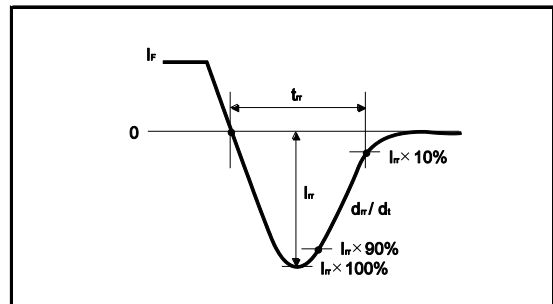
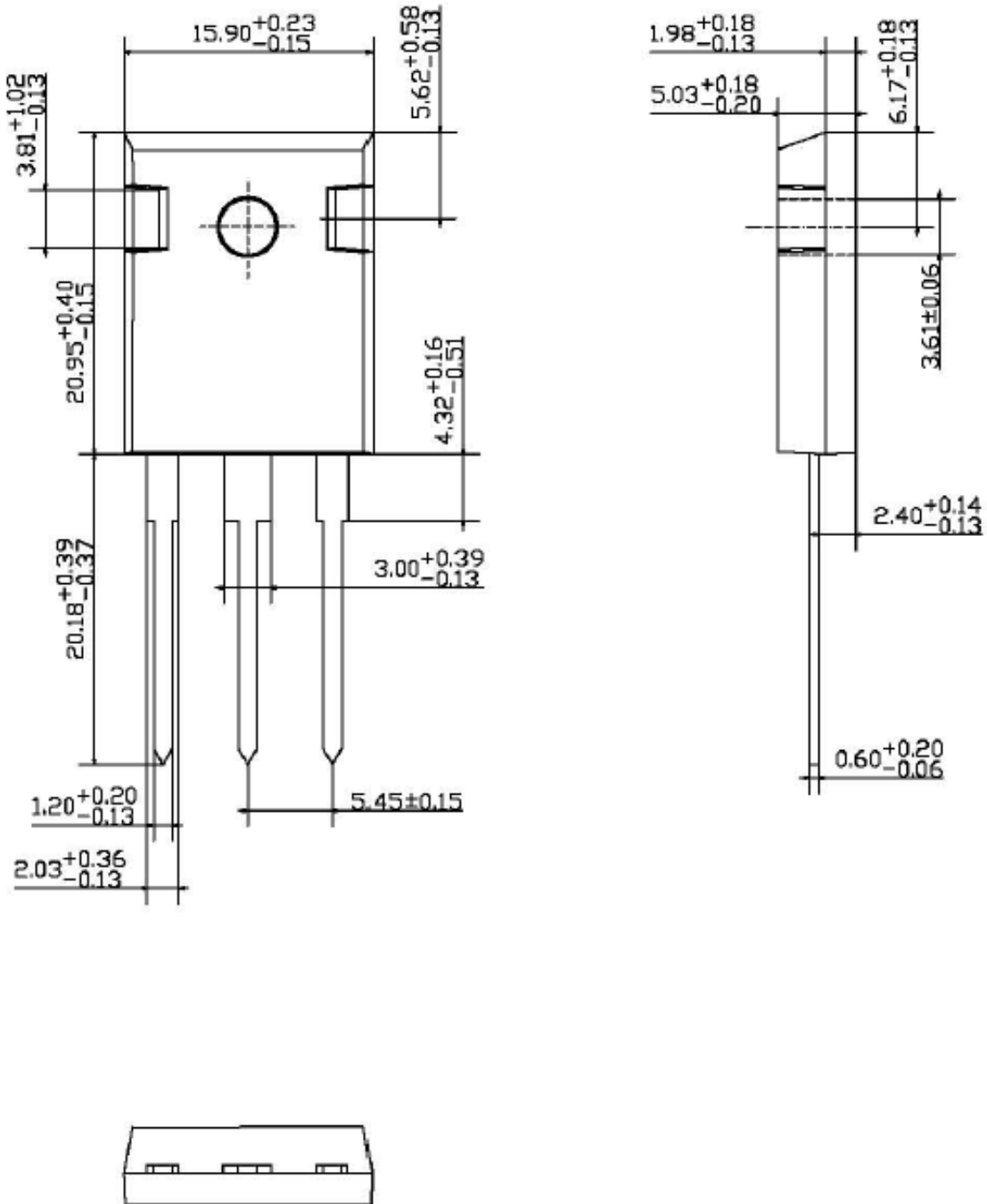


Fig.4-2 Reverse Recovery Waveform



●Dimensions (Unit : mm)

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